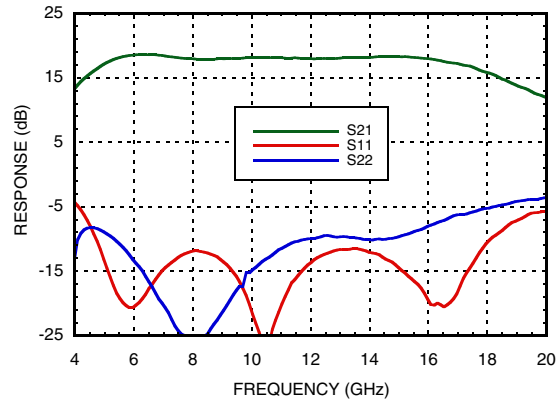
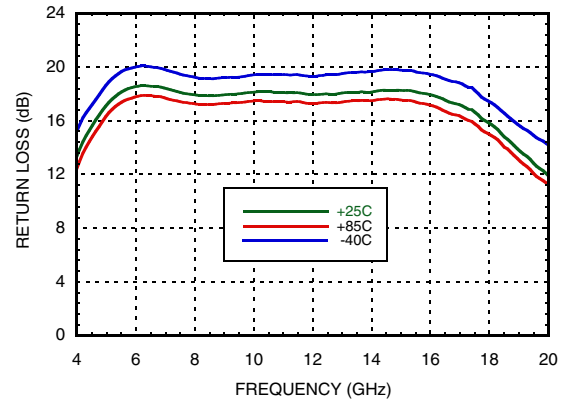
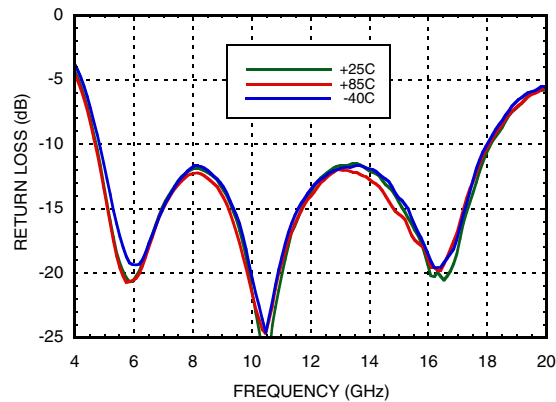
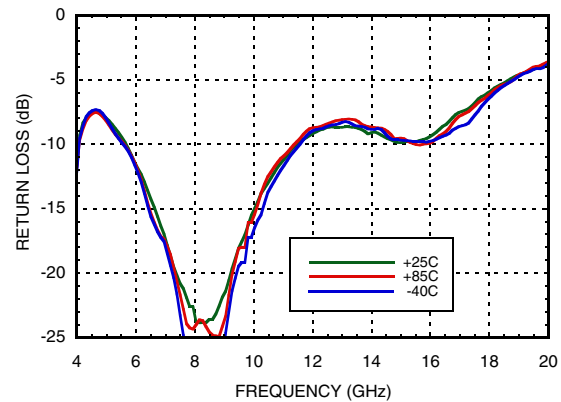
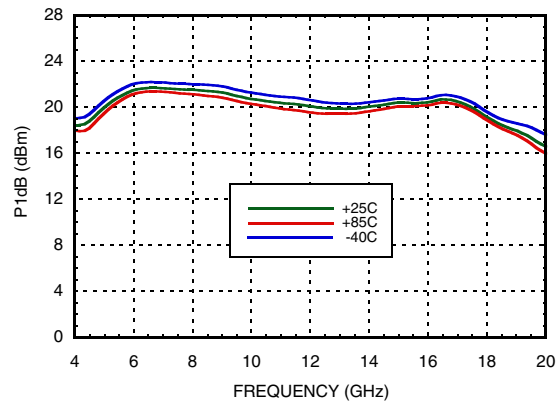
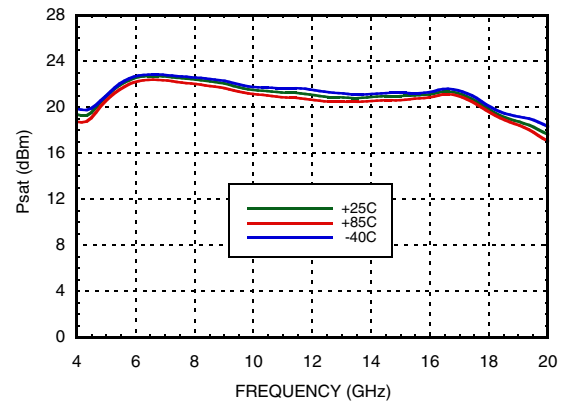
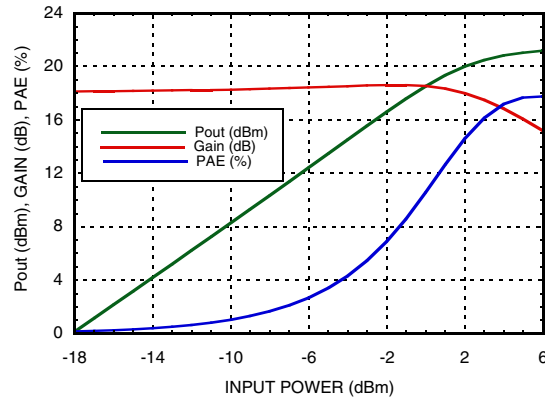
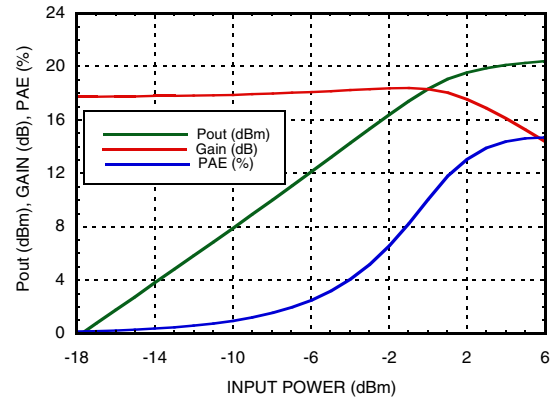
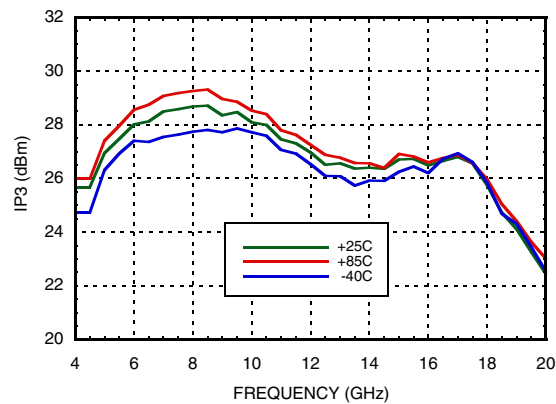
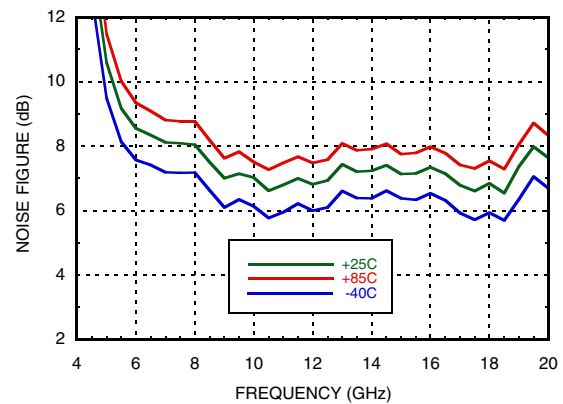
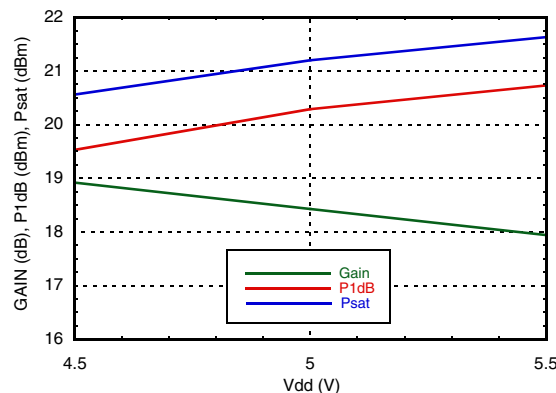
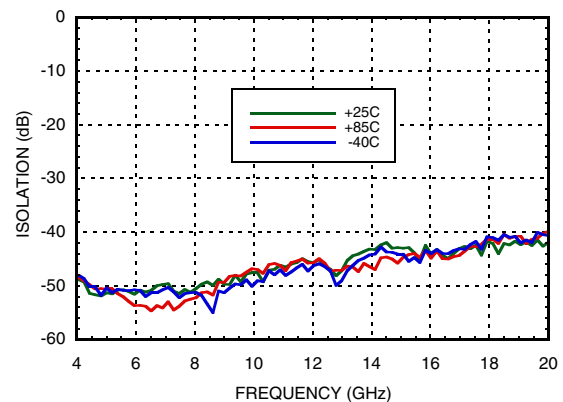


**GaAs PHEMT MMIC MEDIUM
POWER AMPLIFIER, 5 - 18 GHz**
Broadband Gain & Return Loss

Gain vs. Temperature

Input Return Loss vs. Temperature

Output Return Loss vs. Temperature

P1dB vs. Temperature

Psat vs. Temperature


**GaAs PHEMT MMIC MEDIUM
POWER AMPLIFIER, 5 - 18 GHz**
Power Compression @ 10 GHz

Power Compression @ 17 GHz

Output IP3 vs. Temperature

Noise Figure vs. Temperature

**Gain, P1dB & PSAT
vs. Supply Voltage @ 11 GHz**

Reverse Isolation vs. Temperature


**GaAs PHEMT MMIC MEDIUM
POWER AMPLIFIER, 5 - 18 GHz**
Absolute Maximum Ratings

Drain Bias Voltage ($V_{dd1} = V_{dd2}$)	+5.5V
RF Input Power (RFIN)($V_{dd} = +5V_{dc}$)	+10 dBm
Channel Temperature	175 °C
Continuous P_{diss} ($T = 85\text{ °C}$) (derate 12.8 mW/°C above 85 °C)	1.15 W
Thermal Resistance (channel to ground paddle)	78 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A, passed 250V

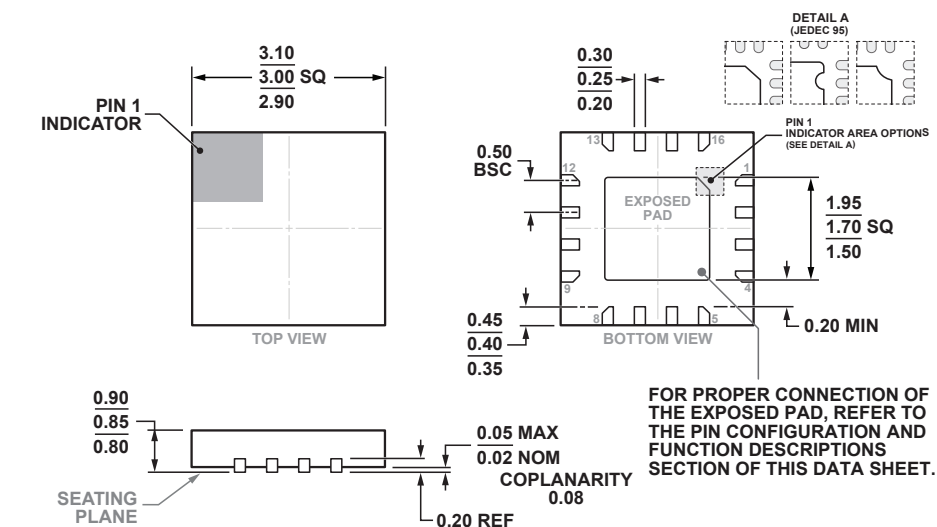
Typical Supply Current vs. $V_{dd1} = V_{dd2}$

$V_{dd1} = V_{dd2}$ (V)	$I_{dd1} + I_{dd2}$ (mA)
+4.5	120
+5.0	122
+5.5	124

Note: Amplifier will operate over full voltage range shown above



**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**

**GaAs PHEMT MMIC MEDIUM
POWER AMPLIFIER, 5 - 18 GHz**
Outline Drawing - HMC451LP3


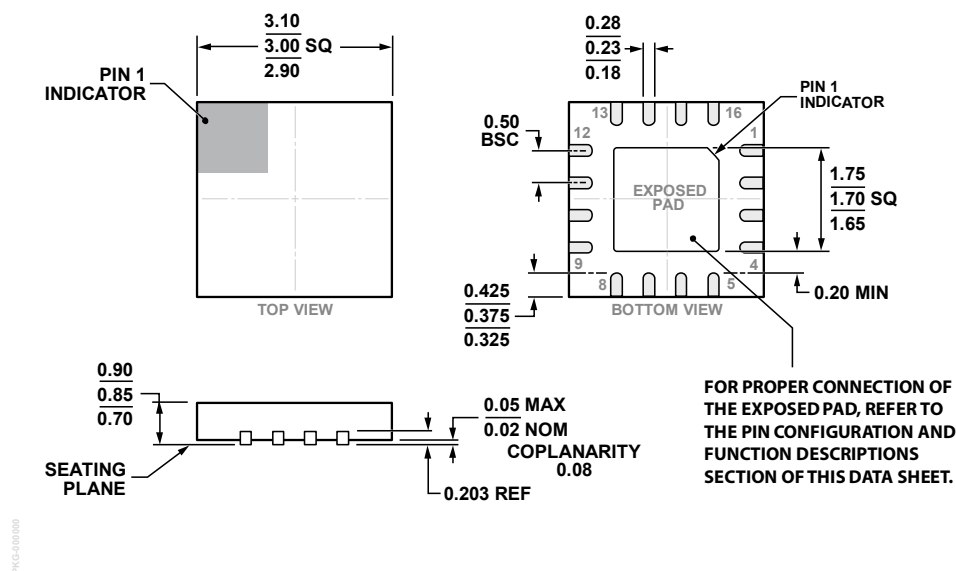
COMPLIANT WITH JEDEC STANDARDS MO-220-VEED-4.

16-Lead Lead Frame chip Scale Package [LFCSP]
3 mm × 3 mm Body and 0.85 mm Package Height
(HCP-16-1)

Dimensions shown in millimeters.

GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 5 - 18 GHz

Outline Drawing - HMC451LP3E



16-Lead Lead Frame chip Scale Package [LFCSP]
3 mm × 3 mm Body and 0.85 mm Package Height
(HCP-16-3)

Dimensions shown in millimeters.

Package Information

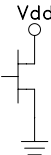
Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[3]
HMC451LP3	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 ^[1]	H451 XXXX
HMC451LP3E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	451 XXXX

[1] Max peak reflow temperature of 235 °C

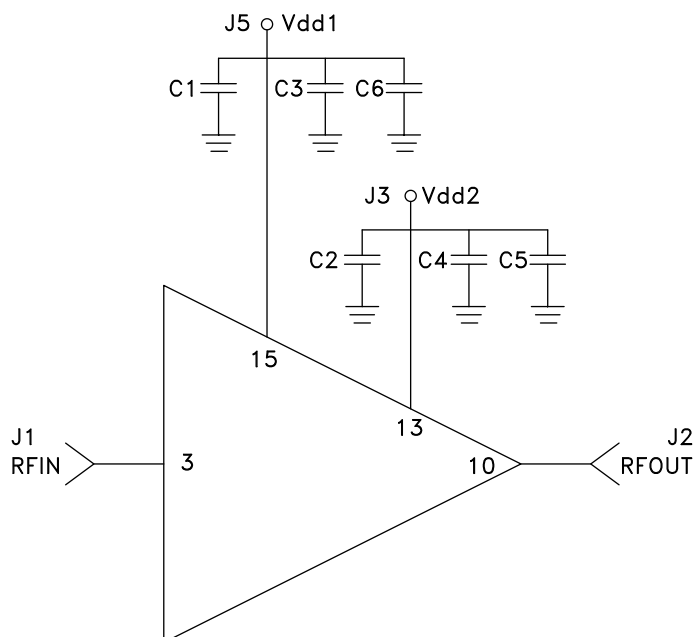
[2] Max peak reflow temperature of 260 °C

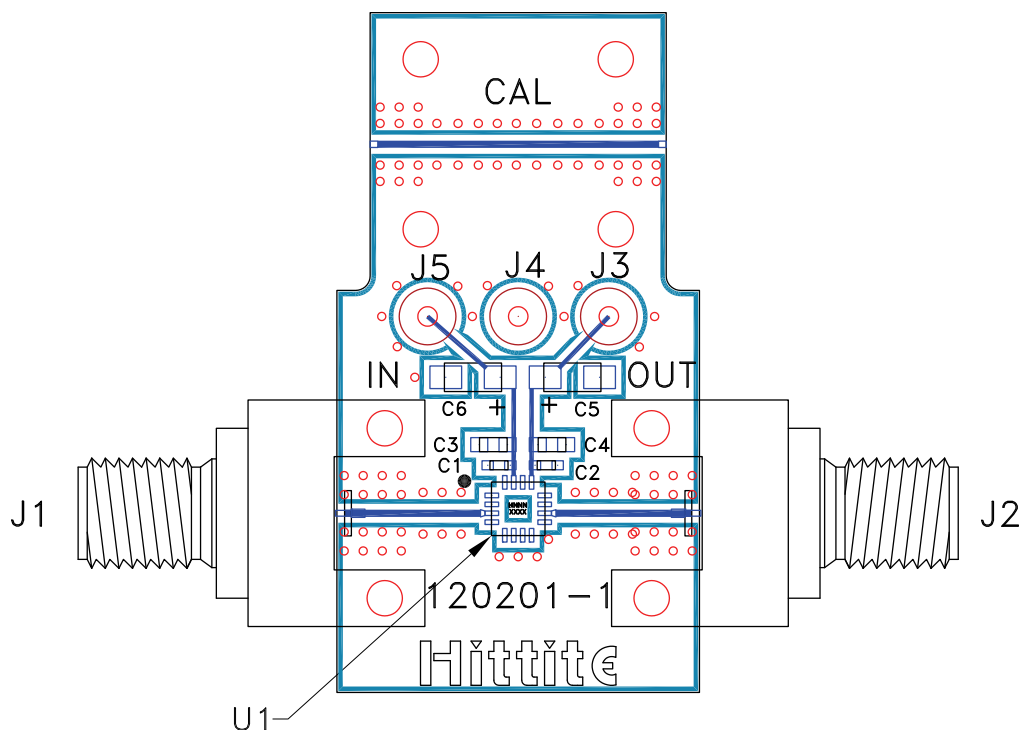
[3] 4-Digit lot number XXXX

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4 - 9, 11, 12, 14, 16	N/C	This pin may be connected to RF/DC ground. Performance will not be affected.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	RFIN 
10	RFOUT	This pin is AC coupled and matched to 50 Ohms.	 RFOUT
13	Vdd2	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1,000 pF and 2.2 μ F are required.	Vdd2 
15	Vdd1	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1,000 pF and 2.2 μ F are required.	Vdd1 
	GND	Package bottom must be connected to RF/DC ground.	 GND

Component	Value
C1, C2	100 pF
C3, C4	1,000 pF
C5, C6	2.2 μ F



**GaAs PHEMT MMIC MEDIUM
POWER AMPLIFIER, 5 - 18 GHz**
Evaluation PCB

List of Materials for Evaluation PCB 120202 ^[1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3 - J5	DC Pin
C1, C2	100 pF Capacitor, 0402 Pkg.
C3, C4	1000 pF Capacitor, 0603 Pkg.
C5, C6	2.2 μ F Capacitor, Tantalum
U1	HMC451LP3(E) Amplifier
PCB [2]	120201 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Arlon 25FR

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices, upon request.